

Octal 3-State Inverting Buffer / Line Driver / Line Receiver in bare die form

Rev 1.1 30/11/21

Description

The 74ACT240 is produced on a 1.5µm 5V CMOS process combining high speed LSTTL performance with CMOS low power. The device can be used as two 4-bit buffers or one 8-bit buffer & features inverting inputs with two output enables, each controlling four of the 3-state outputs. The device is designed to improve performance & density in clock drivers, 3-state memory address drivers & bus orientated transmitters and receivers. Device inputs directly accept TTL without use of pull-up resistors. Inputs are also equipped with protection circuits against static discharge and transient excess voltage.

Ordering Information

The following part suffixes apply:

No suffix - MIL-STD-883 /2010B Visual Inspection

For High Reliability versions of this product please see

54ACT240

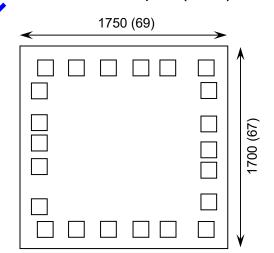
Supply Formats:

- Defaut Die in Waffle Pack (100 per tray capacity)
- Sawn Wafer on Tape On request
- Unsawn Wafer On request
- Die Thickness <> 350µm(14 Mils) On request
- Assembled into Ceramic Package On request

Features:

- Outputs Source/Sink 24mA
- Low input current: 1µA
- Inputs directly accept TTI
- Outputs directly interface CMOS, NMOS and TTL
- Operating voltage rands: 4.5V to 5.5V
- Function compatible with 74FCT240 & 74LS240
- Lower pover alternative to Bipolar or BiCMOS logic
- For non-inversing version pleae see 74ACT244

Die Dimensions in µm (mils)



Mechanical Specification

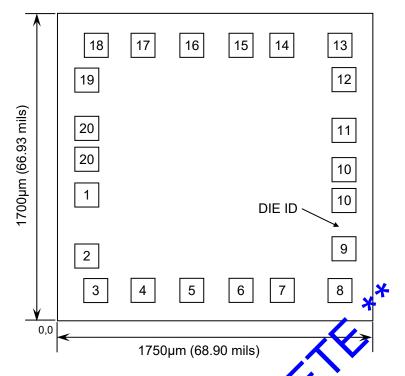
Die Size (Unsawn)	1750 x 1700 69 x 67	μm mils	
Minimum Bond Pad Size	130 x 130 5.12 x 5.12	μm mils	
Die Thickness	350 (±20) 13.78 (±0.79)	μm mils	
Top Metal Composition	Al 1%Si 1.1μ	m	
Back Metal Composition	N/A – Bare Si		



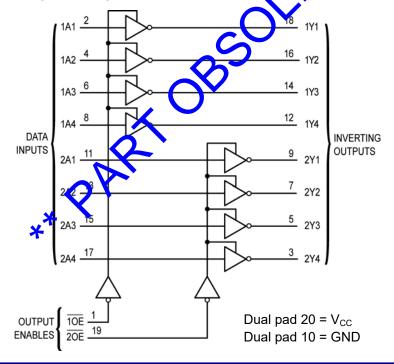


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Pad Layout and Functions



Logic Diagram



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PAD	FUNCTION	COORDINA	ATES (mm)
IAD	TONOTION	Х	Υ
1	10E	0.100	0.630
2	1A1	0.100	0.290
3	2 <u>Y</u> 4	0.150	0.100
4	1/2	0.410	0.100
5	2Y3	0.680	0.100
6	143	0.950	0.100
7	<u>2Y2</u>	1.180	0.100
8	1A4	1.500	0.100
9	2 <u>Y1</u>	1.520	0.330
10	GND	1.520	0.600
10	GND	1.520	0.770
11	2A1	1.520	0.990
12	1Y4	1.520	1.270
13	2A2	1.500	1.460
14	1Y3	1.180	1.460
15	2A3	0.950	1.460
16	1 <u>Y2</u>	0.680	1.460
17	2A4	0.410	1.460
18	1Y1	0.150	1.460
19	20E	0.100	1.270
20	V _{CC}	0.100	1.000
20	V _{CC}	0.100	0.830
CON	NNECT CHIP BA	CK TO V _{CC} O	R FLOAT

Truth Table

INP	OUTPUTS	
10E 20E	1A, 2A	1Y, 2Y
L	L	Н
L	Н	L
Н	X	Z

H = High level (steady state)
L = Low level (steady state)
X = Don't care, Z = High impedance





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Pad Descriptions

ADDRESS INPUTS 1A1, 1A2, 1A3, 1A4, 2A1, 2A2, 2A3, 2A4 (Pads 2, 4, 6, 8, 11, 13, 15, 17)

Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are analysis

CONTROL INPUTS

10E, 20E (Pads 1, 19)

Output enables (active–low). When a low level is applied to these pins, the outputs are enabled and the devices function as inverters. When a high level is applied, the outputs assume the high impedance state.

OUTPUTS

1Y1, 1Y2, 1Y3, 1Y4, 2Y1, 2Y2, 2Y3, 2Y4 (Pads 18, 16, 14, 12, 9, 7, 5, 3)

Device outputs. Depending upon the state of the output enable pins, these outputs are a ther inverting outputs or high–impedance outputs.

Absolute Maximum Ratings¹

9			
PARAMETER	SYMBOL	VALUE	UNIT
DC Supply Voltage (Referenced to GND)	V _{cc}	-0.5 to +7.0	V
DC Input Voltage (Referenced to GND)	¥ V _{IN}	-0.5 to V _{CC} +0.5	V
DC Output Voltage (Referenced to GND)	V _{OUT}	-0.5 to V _{CC} +0.5	V
DC Input Current, per pin	I _{IN}	±20	mA
DC Output Current, per pin	I _{OUT}	±50	mA
DC V _{CC} or GND Current, per pin	I _{CC}	±50	mA
Power Dissipation in Still Air ²	P _D	750	mW
Storage Temperature Range	T _{STG}	-65 to 150	°C

^{1.} Operation above the absolute maximum reting any cause device failure. Operation at the absolute maximum ratings, for extended periods, may reduce device reliability. 2. Measured in plantic DIP package, results in die form are dependent on die attach and assembly method.

Recommended Operating Conditions³ (Voltages referenced to GND)

PARAMETER	SYMBOL	MIN	MAX	UNITS
DC Supply Voltage	V _{CC}	4.5	5.5	V
DC Input or Output Voltage	V _{IN} ,V _{OUT}	0	V _{CC}	V
Operating Tym erature Range	TJ	-40	+85	°C
Output cun ent - High	I _{OH}	-	-24	mA
Output current - Low	I _{OL}	-	24	mA
Input Rise or Fall rate V _{CC} = 4.5V	Δt/ΔV	0	10	ns/V
$(V_{IN} \text{ from 0.8V to 2V})$ $V_{CC} = 5.5V$	ΔųΔV	0	8	113/ V

^{3.} This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND \leq (V_{IN} or V_{OUT}) \leq V_{CC} . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.





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DC Electrical Characteristics (Voltages Referenced to GND)

PARAMETER	SYMBOL	V _{cc} CONDITIONS	LIMITS			UNITS	
			CONDITIONS	25°C	85°C	FULL RANGE	
Minimum High-Level Input Voltage	V _{IH}	4.5V	$V_{OUT} = 0.1V \text{ or } V_{CC}$	2	2	2	V
	VIH	5.5V	-0.1V	2	2	2	
Maximum Low-Level	V _{IL}	4.5V	$V_{OUT} = 0.1V \text{ or } V_{CC}$	0.8	8.0	0.0	V
Input Voltage	V IL	5.5V	-0.1V	0.8	8.0	0.8	, v
		4.5V	Ι _{ΟυΤ} = -50μΑ	4.4	4.4	4.4	V
Minimum High-Level	V _{OH}	5.5V	100130μΑ	5.4	5.4	5.4	V
Output Voltage	V OH	4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^4$	3.86	1.76	3.76	V
		5.5V	$I_{OH} = -24mA$	4.86	4 76	4.76	
Maximum Low-Level Output Voltage	V _{OL}	4.5V	I _{OUT} = 50μA	0.1	0.1	0.1	V
		5.5V		0.1	0.1	0.1	
		4.5V	$V_{IN} = V_{IL} \text{ or } V_{IH}^4$	0.36	0.44	0.44	V
		5.5V	I _{OL} = 24mA	0.36	0.44	0.44	,
Maximum Input Leakage Current	I _{IN}	5.5V	$V_{IN} = V_{CC}$ or GND	±0.1	±1.0	±1.0	μΑ
Maximum 3-State leakage current	I _{OZ}	5.5V	V _{OUT} =V _{CC} or GND V _{IM} =V _{IL} or V _{IH}	±0.5	±2.5	±2.5	μA
Additional Maximum I _{CC} / Input	ΔI _{CCT}	5.5V	V _{IN} = V _{CC} -2.1V	1	1.5	1.5	mA
Minimum Dynamic	I _{OLD}	5.5V	1.65V Max	-	75	75	mA
Output Current ⁶	I _{OHD}	5.5v	V _{OHD} = 3.85V Min	-	-75	-75	111/4
Maximum Quiescent Supply Leakage Current	I _{CC}	3 5V	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0\mu A$	8	40	40	μA

^{4.} $-40^{\circ}\text{C} \le \text{T}_{\text{J}} \le +85^{\circ}\text{C}$ **5.** All outputs loaded, thresholds on input associated with output under test. **6.** Maximum test duration 2.0 ms, one output loaded at a time.

AC Electrical Characteristics⁷

PARAMETER	SYMBOL	IBOL V _{cc} CONDITION	CONDITIONS	LIMITS			UNITS
	OTHIDOL		CONDITIONS	25°C	85°C	FULL RANGE⁴	ONTO
Propagation Delay 1A to 1Y or 2A to 2Y	t _{PLH}	5V ±0.5	5V ±0.5 C _L = 50pF	8.5	9.5	9.5	ns
	t _{PHL}	3V 10.3 CL = 30pi	7.5	8.5	8.5	113	
Output Enable Time	t _{PZH}	5V ±0.5 C ₁ = 50pF	C _L = 50pF	8.5	9.5	9.5	ns
OE to 1Y or 2Y	t _{PZL}	0 10.0	OV 10.0 CL = 30pr	9.5	10.5	10.5	113
Output Disable Time OE to 1Y or 2Y	t _{PHZ}	5V ±0.5	C _L = 50pF	9.5	10.5	10.5	ns
	t _{PLZ}	3 V ±0.5		10	10.5	10.5	113

^{7.} Not production tested in die form, characterized by chip design and tested in package.





Capacitance⁷

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PARAMETER	SYMBOL	V _{cc}	CONDITIONS	TYPICAL	UNITS
Maximum Input Capacitance	C _{IN}	5.0V	T _J = 25°C	4.5	pF
Power Dissipation Capacitance (Per Buffer/Driver)	C _{PD}	5.0V	$T_J = 25$ °C, $C_L = 50$ pF, f = 1MHz	45	pF

7. Not production tested in die form, characterized by chip design and tested in package.

Switching Waveforms

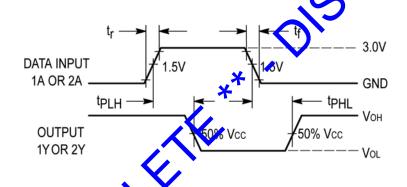


Figure 1 - Propagation Delay - Input 1A or 2A to Output 1Y or 2Y

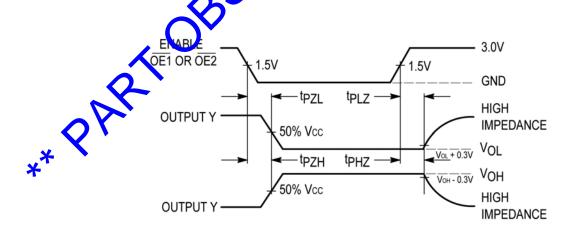


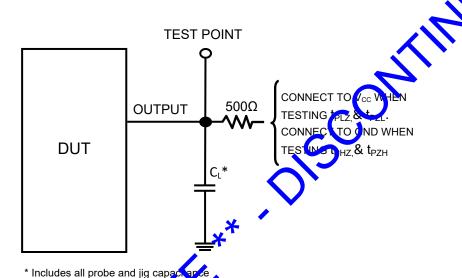
Figure 2 - Propagation Delay - Output Enable to Output 1Y or 2Y





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Test Circuit



Figure

Figure 3

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